

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-44. (cancelled)

45. (previously presented) A process for producing a semiconductor device, comprising:  
\_\_\_\_\_ providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;  
\_\_\_\_\_ wherein an outer peripheral part of said wafer is chamfered in a thickness direction by mechanical chamfering, and  
\_\_\_\_\_ wherein said connecting portions are chamfered in a plane parallel to said main surface by mechanical chamfering.

46. (previously presented) A process for producing a semiconductor device, comprising:  
\_\_\_\_\_ providing wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved

positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;

wherein an outer peripheral part of said wafer is chamfered in a thickness direction by grindstone, and

wherein said connecting portions are chamfered in a plane parallel to said main surface by grindstone.

47. (previously presented) A process for producing a semiconductor device, comprising:

providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular portion and said curved positioning notch, wherein said connecting portions are chamfered in a plane parallel to said main surface; and

positioning said wafer by rotating said wafer.

48. (previously presented) A process for producing a semiconductor device according to claim 47, wherein, in the positioning step, positioning said wafer by using photoelectric elements.

49. (previously presented) A process for producing a semiconductor device according to claim 48, wherein an outer peripheral part

of said wafer is chamfered in a thickness direction by mechanical chamfering,  
and

wherein said connecting portions are chamfered in a plane parallel to  
said main surface by mechanical chamfering.

50. (previously presented) A process for producing a  
semiconductor device according to claim 48, wherein an outer peripheral part  
of said wafer is chamfered in a thickness direction by grindstone, and  
wherein said connecting portions are chamfered in a plane parallel to  
said main surface by grindstone.

51. (previously presented) A process for producing a  
semiconductor device according to claim 47, wherein, in the positioning step,  
positioning said wafer by optical means.

52. (previously presented) A process for producing a  
semiconductor device according to claim 47, wherein an outer peripheral part  
of said wafer is chamfered in a thickness direction by mechanical chamfering,  
and  
wherein said connecting portions are chamfered in a plane parallel to  
said main surface by mechanical chamfering.

53. (previously presented) A process for producing a  
semiconductor device according to claim 47, wherein an outer peripheral part  
of said wafer is chamfered in a thickness direction by grindstone, and

wherein said connecting portions are chamfered in a plane parallel to  
said main surface by grindstone.

54-60. (cancelled)